Amendments To The Claims:

1. (Currently Amended) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

~~silicon dioxide, wherein the silicon dioxide is~~ colloidal silica ~~or fumed silica~~;

wherein, ~~when the silicon dioxide is colloidal silica,~~ an average primary particle diameter D_{SA} of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter D_{N4} of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

~~wherein, when the silicon dioxide is fumed silica, an average primary particle diameter D_{SA} of the fumed silica, which is obtained from a specific surface area of the fumed silica measured by a BET method, is from 5 to 30 nm; and wherein an average secondary particle diameter D_{SA} of the fumed silica, which is measured by a laser scattering method, is from 5 to 200 nm;~~

an alkaline compound;

a water-soluble polymer; and

water.

2. (Currently Amended) The polishing composition according to claim 1, wherein the average primary particle diameter D_{SA} of the colloidal silica ~~and the fumed silica~~ is from 5 to 25 nm.

3. (Currently Amended) The polishing composition according to claim 2, wherein the average primary particle diameter D_{SA} of the colloidal silica ~~and the fumed silica~~ is from 5 to 20 nm.

4. (Original) The polishing composition according to claim 1, wherein the average secondary particle diameter D_{N4} of the colloidal silica is from 5 to 100 nm.

5. (Original) The polishing composition according to claim 4, wherein the average

secondary particle diameter D_{N4} of the colloidal silica is from 5 to 80 nm.

6. (Canceled) The polishing composition according to claim 1, wherein the silicon dioxide is colloidal silica.

7. (Original) The polishing composition according to claim 1, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene oxide.

8. (Original) The polishing composition according to claim 7, wherein the water-soluble polymer is hydroxyethyl cellulose.

9. (Original) The polishing composition according to claim 8, wherein content of the hydroxyethyl cellulose in the polishing composition is from 0.005 to 1.5 wt%.

10. (Original) The polishing composition according to claim 1, wherein the alkaline compound is at least one selected from potassium hydroxide, sodium hydroxide, ammonia, tetramethylammonium hydroxide, anhydrous piperazine, and piperazine hexahydrate.

11. (Withdrawn) A method of polishing a wafer, the method comprising:

preparing a polishing composition, wherein the polishing composition includes:

silicon dioxide, wherein the silicon dioxide is colloidal silica or fumed silica;

wherein, when the silicon dioxide is colloidal silica, an average primary particle diameter D_{SA} of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter D_{N4} of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

wherein, when the silicon dioxide is fumed silica, an average primary particle diameter D_{SA} of the fumed silica, which is obtained from a specific surface area of the fumed silica measured by a BET method, is from 5 to 30 nm, and wherein an average

secondary particle diameter D of the fumed silica, which is measured by a laser scattering method, is from 5 to 200 nm;

an alkaline compound;

a water-soluble polymer; and

water; and

precision polishing a surface of the wafer using the polishing composition.

12. (New) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

fumed silica, wherein an average primary particle diameter D_{SA} of the fumed silica, which is obtained from a specific surface area of the fumed silica measured by a BET method, is from 5 to 25 nm; and wherein an average secondary particle diameter D_{N4} of the fumed silica, which is measured by a laser scattering method, is from 5 to 200 nm;

an alkaline compound;

a water-soluble polymer; and

water.

precision polishing a surface of the wafer using the polishing composition.

13. (New) The polishing composition according to claim 12, wherein the average primary particle diameter D_{SA} of the fumed silica is from 5 to 20 nm.

14. (New) The polishing composition according to claim 12, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene oxide.

15. (New) The polishing composition according to claim 14, wherein the water-soluble polymer is hydroxyethyl cellulose.

16. (New) The polishing composition according to claim 15, wherein content of the hydroxyethyl cellulose in the polishing composition is from 0.005 to 1.5 wt%.

17. (New) The polishing composition according to claim 12, wherein the alkaline compound is at least one selected from potassium hydroxide, sodium hydroxide, ammonia, tetramethylammonium hydroxide, anhydrous piperazine, and piperazine hexahydrate.